

15. The power semiconductor device according to claim **13**, wherein the field plate electrode is connected to one of the second major electrode and the control electrode.

16. The power semiconductor device according to claim **13**, wherein corner of the trench formed at outer side of a termination section is rounded.

17. The power semiconductor device according to claim **16**, wherein the sixth second-conductivity-type semiconductor layer formed in the termination section is formed deeper than the sixth second-conductivity-type semiconductor layer formed in a cell section.

18. The power semiconductor device according to claim **17**, wherein impurity concentration in the second first-conductivity-type semiconductor layer and the third second-conductivity-type semiconductor layer formed in the termination

section is lower than impurity concentration in the second first-conductivity-type semiconductor layer and the third second-conductivity-type semiconductor layer formed in the cell section.

19. The power semiconductor device according to claim **16**, wherein the sixth second-conductivity-type semiconductor layer is formed to entirely cover side face of a portion buried in the semiconductor substrate in the second main electrode.

20. The power semiconductor device according to claim **16**, wherein a plurality of portions in the second major electrode are buried in the termination section and width of the each portion is equal to width of a portion of the second major electrode buried in a cell section.

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